

## X-Band Diode Limiter

### ■ GENERAL DESCRIPTION

NJS6930A is designed for the high power limiter of radar system.

It features a small size operable at any frequency between 9.30GHz and 9.50GHz.

This diode limiter consists of the two stage limiter diodes. And insertion loss can be controlled for STC function by the external bias current, which flows the second limiter diode.



### ■ MAXIMUM AND MINIMUM RATINGS

PARAMETERS	Min.	Max.	Units
Maximum handling power		30	kW
Ambient temperature	-30	+90	°C
RF pulse width	-	1.5	µs
Bias current	-	5	mA

### ■ ELECTRICAL CHARACTERISTICS < at 25 °C >

PARAMETERS	Min.	Max.	Units
V.S.W.R. (Note 1,3)	-	1.5	-
Insertion loss (Note 1,3)		1.5	dB
Flat leakage power (Note 2,3)		150	mW
Spike leakage power (Note 2,3)		600	mW
Recovery to -3dB (Note 2,3)		0.5	µs
Variable attenuation range (Note 1,3)			
latt= 10 uA	6	12	dB
latt= 1 mA	28	34	dB

Note 1: Measured at power level 0.1mW CW.

Note 2: Measured at power level 3kW, 1.0usec pulse width and 1000pps.

Note 3: Measured at frequency 9.40GHz.

NJS6930A ATTENUATION

f=9410MHz,P=-10dBm

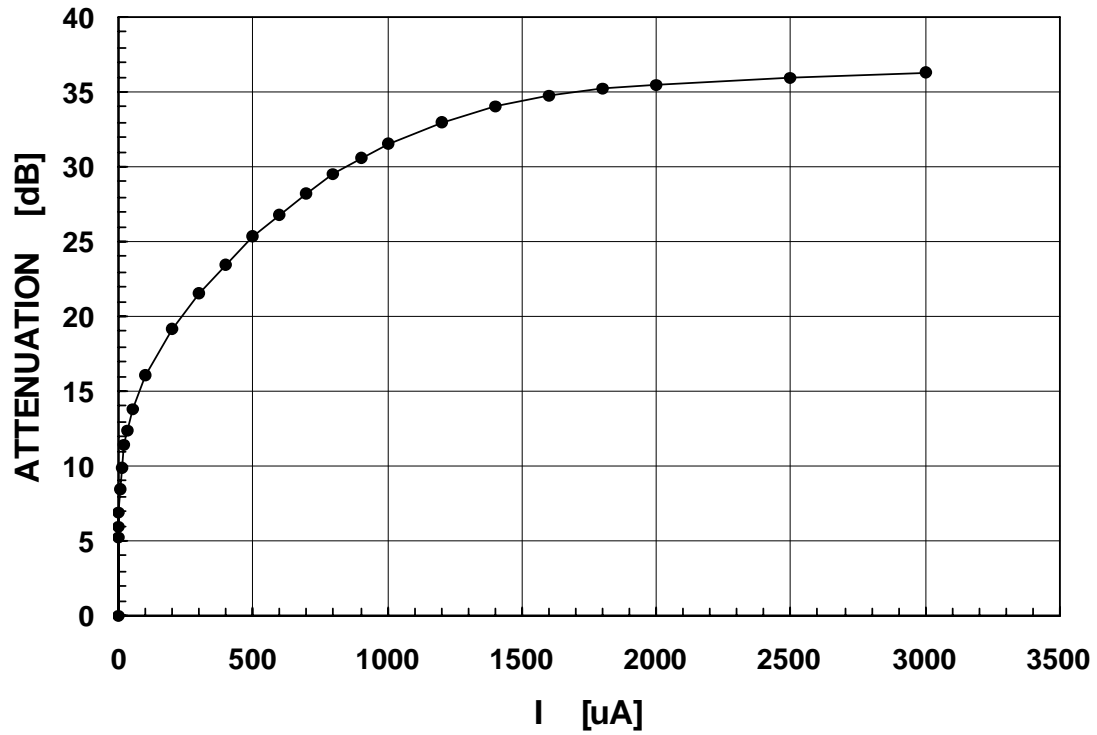
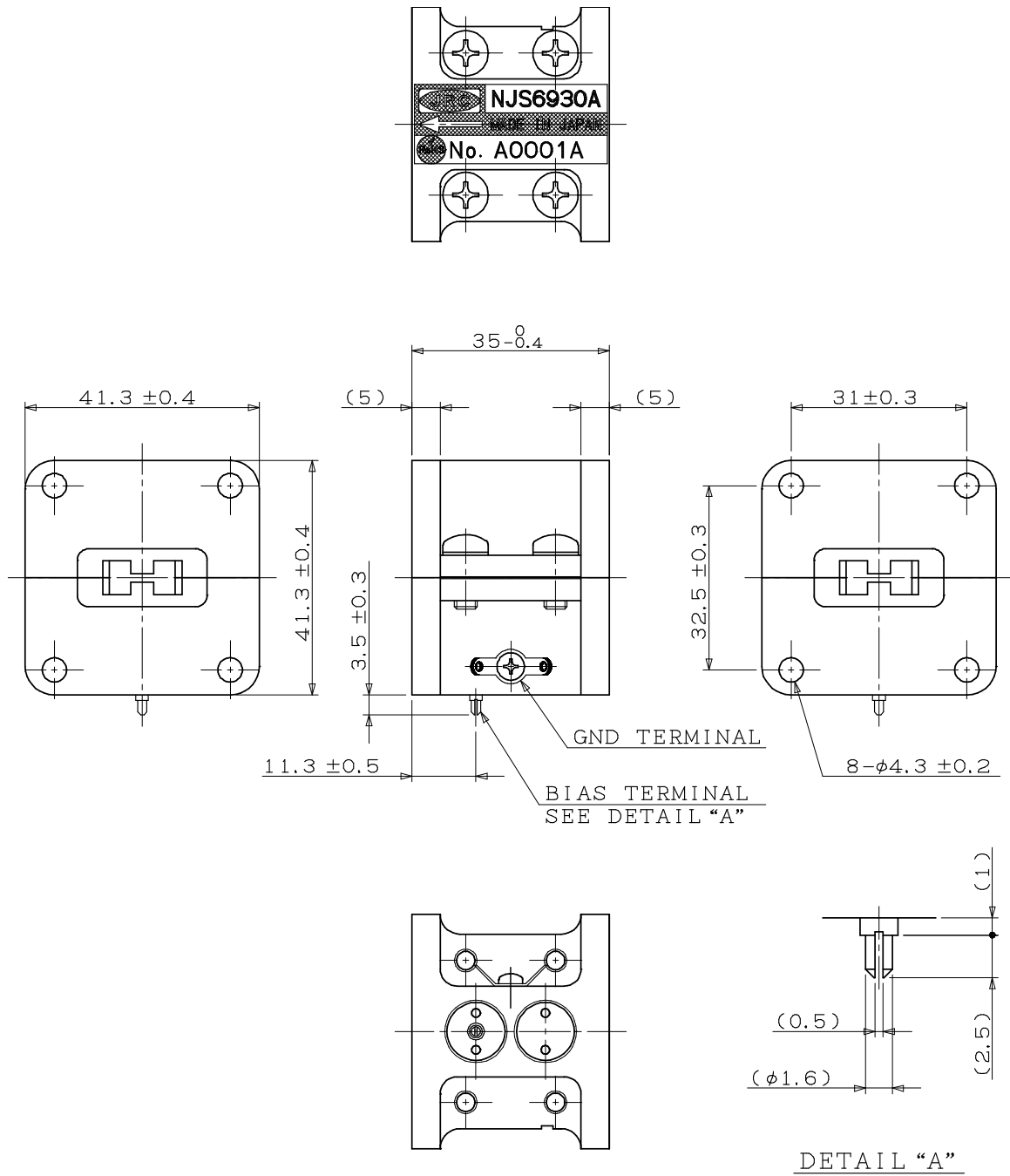


Fig.1 ATTENUATION CURVE

■ OUTLINE



(Dimensions are expressed in "mm".)

\*Note : The contents of this sheet are subject to change without notice.